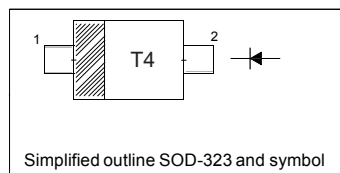


Silicon Epitaxial Planar Switching Diode

PINNING

PIN	DESCRIPTION
1	Cathode
2	Anode



Characteristics at $T_a = 25^\circ\text{C}$

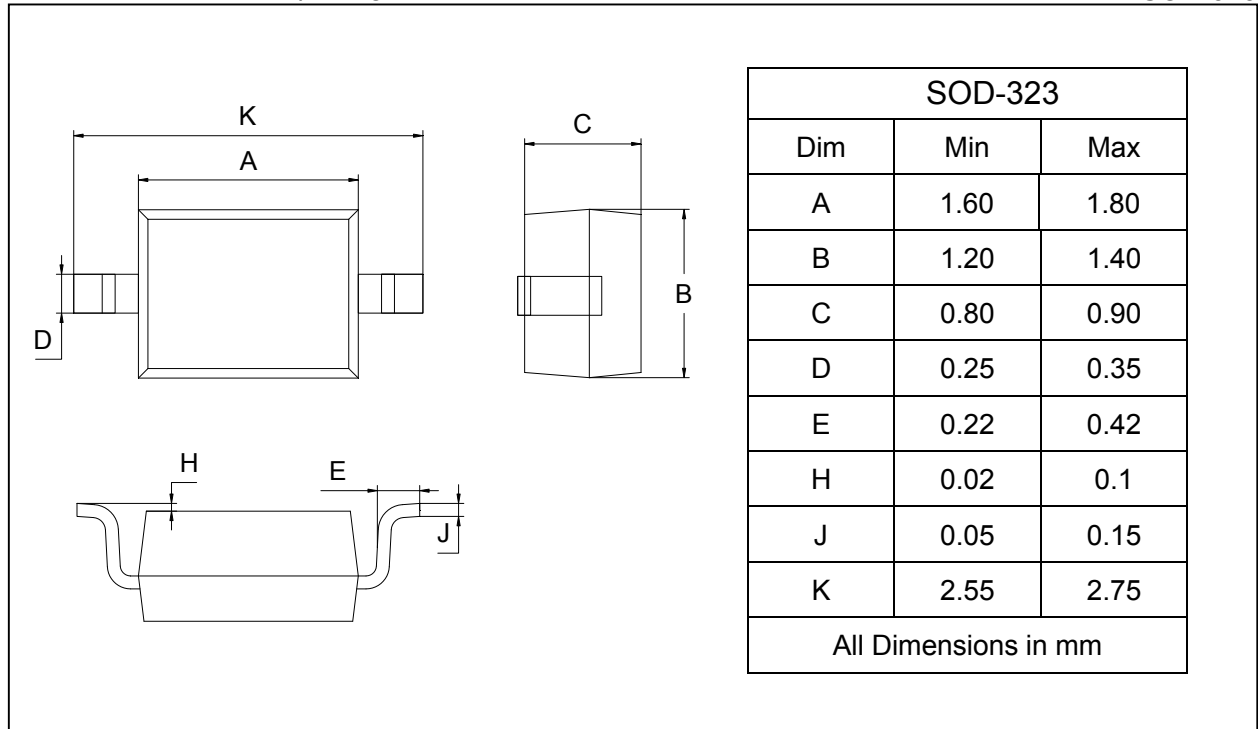
Parameter	Symbol	Min.	Max.	Unit
Reverse Breakdown Voltage at $I_R = 1\ \mu\text{A}$	$V_{(BR)R}$	75	-	V
Forward Voltage at $I_F = 1\ \text{mA}$ at $I_F = 10\ \text{mA}$ at $I_F = 50\ \text{mA}$ at $I_F = 150\ \text{mA}$	V_F	- - - -	0.715 0.855 1 1.25	V
Peak Reverse Current at $V_R = 75\ \text{V}$ at $V_R = 20\ \text{V}$ at $V_R = 75\ \text{V}$, $T_J = 150^\circ\text{C}$ at $V_R = 25\ \text{V}$, $T_J = 150^\circ\text{C}$	I_R	- - - -	1 25 50 30	μA nA μA μA
Total Capacitance at $V_R = 0\ \text{V}$, $f = 1\ \text{MHz}$	C_T	-	2	pF
Reverse Recovery Time at $I_{rr} = 0.1 \times I_R$, $I_F = I_R = 10\ \text{mA}$, $R_L = 100\ \Omega$	t_{rr}	-	4	ns

Absolute Maximum Ratings ($T_a = 25^\circ\text{C}$)

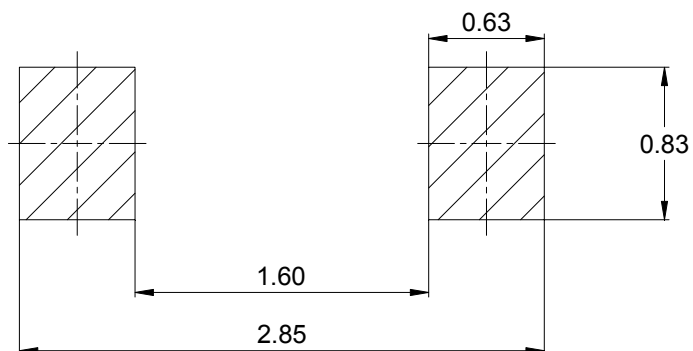
Parameter	Symbol	Value	Unit
Peak Reverse Voltage	V_{RM}	100	V
Reverse Voltage	V_R	75	V
Average Rectified Forward Current	$I_{F(AV)}$	150	mA
Surge Forward Current ($t < 1\ \text{s}$, $T_J = 25^\circ\text{C}$)	I_{FSM}	350	mA
Power Dissipation	P_{tot}	200	mW
Thermal Resistance from Junction to Ambient Air	$R_{\theta JA}$	625	$^\circ\text{C/W}$
Junction Temperature	T_J	150	$^\circ\text{C}$
Storage Temperature Range	T_{stg}	- 65 to + 150	$^\circ\text{C}$

Plastic surface mounted package

SOD-323



SOLDERING FOOTPRINT



Unit : mm

Typical Characteristics

